

# 2SC4046

Silicon NPN Epitaxial

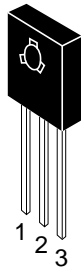
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## Application

High voltage amplifier

## Outline

TO-126 MOD



1. Emitter
2. Collector
3. Base

## Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	120	V
Collector to emitter voltage	$V_{CEO}$	120	V
Emitter to base voltage	$V_{EBO}$	5	V
Collector current	$I_C$	0.2	A
Collector power dissipation	$P_C^{*1}$	8	W
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

Note: 1. Value at  $T_c = 25^\circ\text{C}$

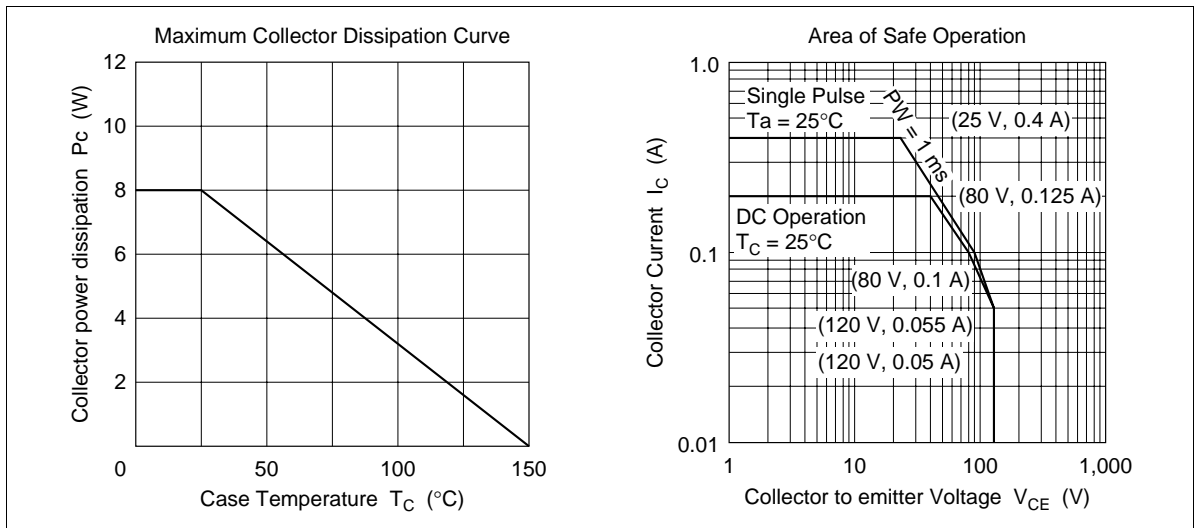
# 2SC4046

## Electrical Characteristics (Ta = 25°C)

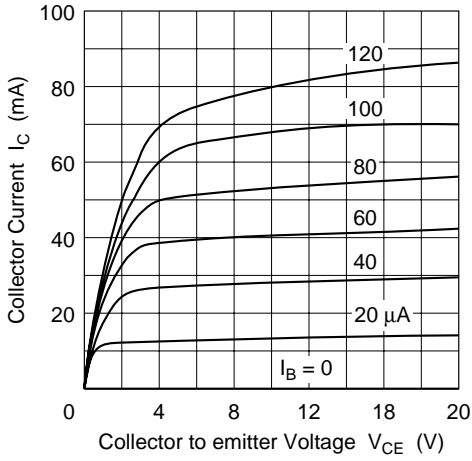
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	120	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	120	—	—	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	10	$\mu A$	$V_{CB} = 80 \text{ V}, I_E = 0$
DC current transfer ratio	$h_{FE}^{*1}$	250	—	800		$V_{CE} = 5 \text{ V}, I_C = 10 \text{ mA}$
Base to emitter voltage	$V_{BE}$	—	—	1.0	V	
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.0	V	$I_C = 200 \text{ mA}, I_B = 20 \text{ mA}$
Gain bandwidth product	$f_T$	—	350	—	MHz	$V_{CE} = 10 \text{ V}, I_C = 50 \text{ mA}$
Collector output capacitance	$C_{ob}$	—	3.5	—	pF	$V_{CB} = 30 \text{ V}, f = 1 \text{ MHz}, I_E = 0$

Note: 1. The 2SC4046 is grouped by  $h_{FE}$  as follows.

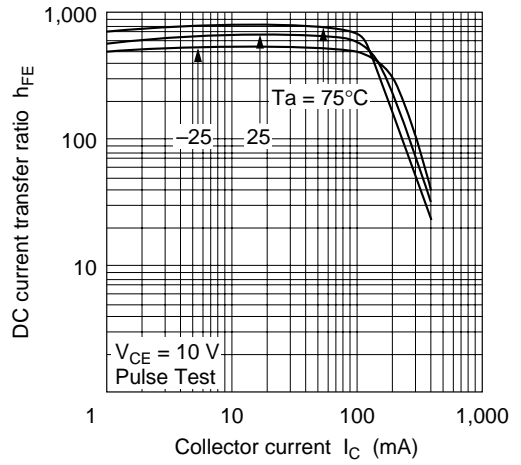
Grade	D	E
$h_{FE}$	250 to 500	400 to 800



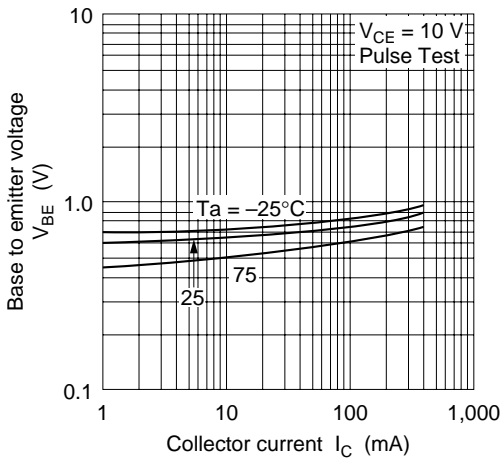
Typical Output Characteristics



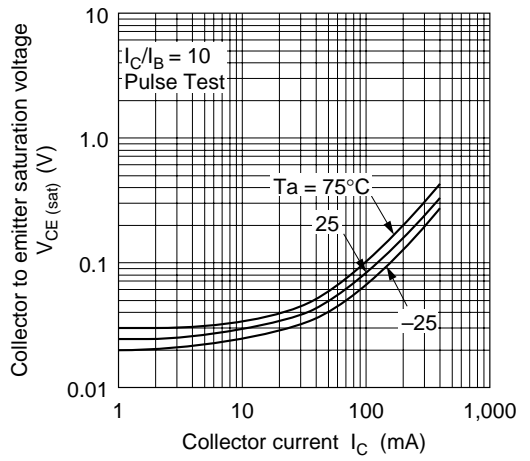
DC Current Transfer Ratio vs. Collector Current



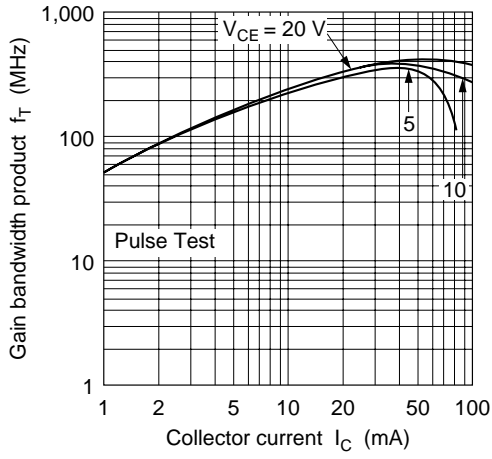
Base to Emitter Voltage vs. Collector Current



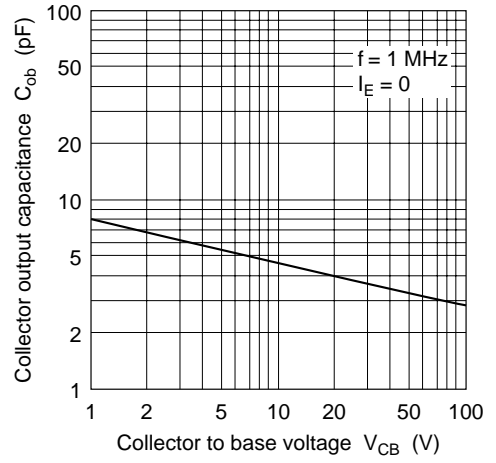
Collector to Emitter Saturation Voltage vs. Collector Current

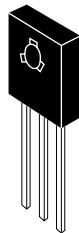
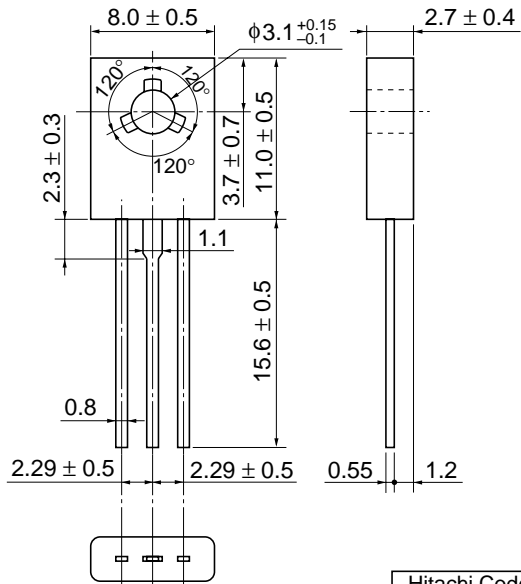


Gain Bandwidth Product vs. Collector Current



Collector Output Capacitance vs. Collector to Base Voltage





Hitachi Code	TO-126 Mod
JEDEC	—
EIAJ	—
Weight (reference value)	0.67 g

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